

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



In re the application of: Nam-Kyeong KIM, et al.

Serial No.: 10/613,993

Group Art Unit: 2826

Filed: July 8, 2003

Examiner: Tran, Tan N.

For: CAPACITOR AND METHOD FOR FABRICATING FERROELECTRIC MEMORY
DEVICE WITH THE SAME

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RESPONSE TO RESTRICTION REQUIREMENT

Honorable Commissioner for Patent
P.O. Box 1450
Alexandria, VA 22313-1450

March 4, 2004

Sir:

In response to the Request for Restriction mailed February 13, 2004 (Paper No. 20040101), Applicant elects Group II, claims 8-14, drawn to a method of manufacturing a semiconductor device, classified in class 438, subclass 3, with traverse.

Applicant respectfully traverses the restriction requirement. The claims of Group I (Claims 1-7) drawn to a semiconductor device and the claims of Group II (Claims 8-14) drawn to a method of manufacturing a semiconductor device are closely related to each other and define a single invention. The semiconductor device defined in claims 1-7 is manufactured by the process of claims 8-14, and thus, claims 1-14 define a single inventive concept. Further, Applicant respectfully submits that it would not be unduly burdensome for the Examiner to examine the claims of both groups. Applicant respectfully requests that claims 1-14 be examined.

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Atty. Docket No.: P68980US0

An early Office Action on the merits is respectfully requested.

If a Petition for Extension is necessary and the petition and/or payment of the fee(s) is not enclosed, this will act as a petition to extend the time for response and authorization to charge the necessary fee(s) under 37 CFR 1.17(a)-(d) to Deposit Account 06-1358.

Respectfully submitted,



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